



## MAINTENANCE MANUAL

25--50 MHz RF ASSEMBLY I9D4I6478GI - G4

AND

MIXER/IF/NOISE BLANKER BOARD I9D4I6562GI - G4

LBI499IG  
(DF1107)

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## DESCRIPTION

The RF Assembly uses two tuned helical resonators and four L-C tuned circuits to provide front end selectivity.

The Mixer/IF/Noise Blanker board (MIF/NB) uses the RF input from the RF Assembly and the mixer injection frequency from the oscillator/multiplier board to generate the IF frequency. The noise blanker eliminates undesirable noise interference in the received audio.

## RF AMPLIFIER A302

RF Amplifier Q1 is a Field-Effect Transistor (FET). Q1 operates as a grounded gate amplifier, with the RF input applied to the "source" terminal. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled through four L-C tuned circuits (L1-C7, L2-C8, L3-C9 and L4-C10) to the mixer. The four tuned circuits and the two helical resonators provide the receiver front end selectivity.

## CIRCUIT ANALYSIS

### MIXER/IF/NOISE BLANKER

#### RF ASSEMBLY

##### ANTENNA INPUT A301A/A301B

An RF signal is applied from the antenna input circuit (L551) of the noise blanker section of the MIF/NB board to A301-J1. The antenna input circuit provides an AC ground between vehicle ground and receiver A-. Resistor R1 prevents a static charge from building up on the vehicle antenna. The output of A301 is coupled through two high-Q helical resonators (L301, C301 and L302, C302) to the RF amplifier. The coils are tuned to the incoming frequency by C301 and C302. Lamp DS1 protects the RF amplifier stage against an excessive RF input.

#### MIXER & CRYSTAL FILTER

The mixer uses a FET (Q501) as the active device. The FET mixer provides a high input impedance, high power gain, and an output relatively free of harmonics (low in intermodulation products).

In the mixer stage, RF from the RF amplifier stage is coupled through tuned circuit L501 and C502 which matches the RF output to the gate of mixer Q501. Injection voltage from the multiplier-selectivity stages is inductively coupled through L502 to the source of the mixer. The mixer IF output signal is coupled from the drain of Q501 through a tuned circuit (L504 and C511) to the first FET noise blanker gate Q502. The IF signal is then coupled through a tuned circuit (L506 and C517) to the second FET noise blanker gate Q503.

During the presence of impulse noise from the antenna, the noise blanker circuit (U551) provides a positive pulse to the gates of Q502 and Q503 which attenuates the IF signal during the noise pulse period (see Noise Blanker description for details). This eliminates undesirable noise interference in the received audio without degrading receiver performance.

The mixer IF output signal is then coupled to the input of the four-pole monolithic crystal filter. The highly selective crystal filter (FL501 and FL502) provides the first portion of the receiver IF Selectivity. The output of the crystal filter is coupled through impedance-matching network Z502 (L520 and C501) to IF Amplifier Q520.

Service Note: Variable capacitor C521 does not require adjustment when performing normal alignment. If the four-pole monolithic crystal filter is replaced, then adjustment of C521 is necessary for optimum IF response.

#### IF AMPLIFIER

IF amplifier Q520 is a dual-gate FET. The crystal filter output is applied to Gate 1 of the amplifier, and the output is taken from the drain. The biasing on Gate 2 and the drain load determines the gain of the stage. The amplifier provides approximately 20 dB of IF gain. The output of Q520 is coupled through a network (L521 and C528) that matches the amplifier output to the next IF stage. The output of the MIF/NB board is applied through feed-through capacitor C305 to the next IF stage or to the MIF switch when a dual front end is used.

Supply voltage for the RF amplifier and MIF/NB board is supplied through feed-through capacitor C306.

#### NOISE BLANKER

An RF signal and noise pulse from the antenna (J551) fed simultaneously to the Noise Blanker 1st RF Amplifier and the RF Assembly (A302) RF Amplifier. The signal and noise is transformer coupled through L551 to the 1st RF amplifier Q551 (dual-gate FET). The input signal is applied to Gate 1 of the amplifier, and the output is taken from the drain. The biasing of Gate 2 and the drain load determines the gain of the stage. The signal is then coupled through tuned circuits L552/C558 and L553/C560 to the 2nd RF amplifier Q552, which is also a dual-gate FET. The combined gain of Q551 and Q552 is approximately 50 dB.

The amplified signal is coupled through tuned circuit L554/C564 to pulse detector/amplifier/switch IC (U551). IC (U551) is

a custom hybrid integrated circuit which contains a pulse detector, pulse amplifier, pulse amplifier/switch, intermodulation detector and a blanker disable switch. The IC functions as a pulse detector and processing circuit for the noise blanker. Regulated 10 VDC, which powers U551, is applied through pin 3. The associated capacitors (C571, C572 and C574) provide emitter decoupling for various stages of the IC.

#### Pulse Detector

The impulse noise from the RF amplifier is applied to pin 6 of U551 through tuned circuit L554/C564 to the pulse detector. Bias for the detector is established by R563, R564 and CR551. Diode CR551 is normally conducting, thus biasing the pulse detector. A positive pulse applied to the pulse detector causes it to conduct heavily. The output of the detector is a negative going pulse that is relatively free of any RF components. The pulse detector metering point (Blanker Meter) connects from pin 2 of U551 thru P553 to J605 on the next IF stage (J2305 on MIF switch when a DFE is used) and serves as a convenient measuring point when performing alignment.

#### Pulse Amplifier and Noise Blanker Disable Switch

The negative pulse output from the pulse detector turns the pulse amplifier on, producing a positive output pulse. The threshold point of the pulse amplifier and the RF gain of the 1st and 2nd RF amplifier stages (Q551 and Q552) in the noise blanker circuit prevent noise blanking due to any low-level inherent receiver noise.

A noise blanker disable switch provides a means for manually disabling the noise blanker circuits. Connecting pin 4 of U551 to A- turns the disable switch on, which in turn inhibits the pulse amplifier. The blanker disable function is also provided at pin 5 of the system plug (P904) for external control.

#### Pulse Amplifier/Switch

The positive output pulse from the pulse amplifier is fed to the pulse amplifier/switch. This circuit functions as a constant width pulse generator whose output is a positive 6 Volt pulse with a duration of 2 microseconds. This pulse is applied from pin 11 of U551 to the noise blanker gates (Q502 and Q503).

Noise blanker gates Q502 and Q503 are turned ON (conducting) during the presence of the noise blanking pulse. These gates present a low impedance RF path to A- for the pulse duration (approximately 3 microseconds), providing approximately 60 dB attenuation of the IF signal and the impulse noise present. As the noise signal from the antenna is applied to the noise blanker circuits, the RF signal is also applied to

the receiver RF input. The inherent delay presented to the received RF signal and the impulse noise by the helical resonators in the receiver RF assembly (L301 and L302) and the four tuned circuits (L1/C7 through L4/C10) allows the noise blanking pulse to turn on the blanking gates. This attenuates the received signal just prior to the arrival of the impulse noise.

#### Intermodulation (IM) Detector

The output of the pulse amplifier is also applied to the IM detector. The IM detector does not respond to noise pulses appearing at its input because of the cir-

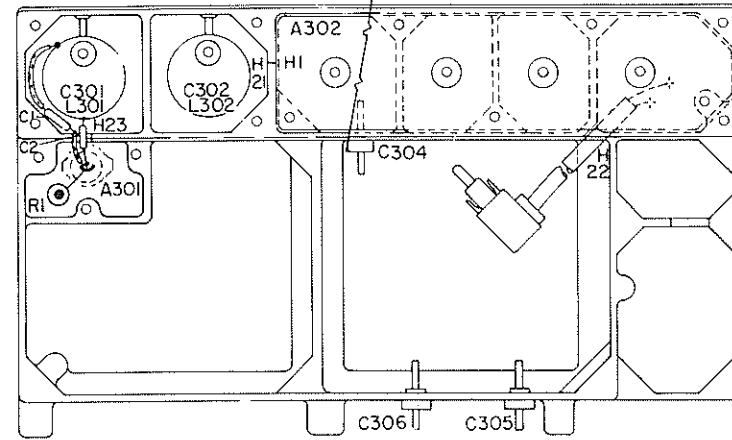
cuit design utilized, but the detector is activated during the presence of a sinusoidal signal. This sinusoidal signal is the beat frequency difference of two signals present in the noise blanker channel.

A resultant AGC voltage (approximately +3 VDC) is developed through the integrating action of C573 and is applied from pin 13 of U551 to the 2nd RF amplifier (Q552) of the noise blanker circuit. This action sufficiently reduces the gain of the noise blanker RF stage (Q552) so that receiver performance is not degraded by blanking pulses which would create receiver intermodulation close to the receiver operating frequency.

GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION  
WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.

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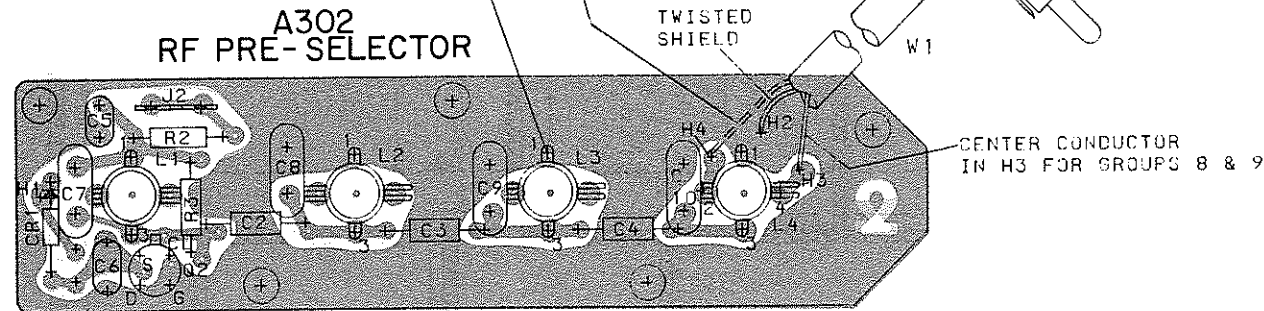
# RF ASSEMBLY BOTTOM VIEW



CENTER CONDUCTOR  
IN H4 FOR GROUPS 1 THRU 4

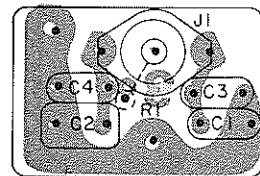
RAISED TAB ON  
COIL FORM INDICATES  
PIN 1 ON L1 - L4

## A302 RF PRE-SELECTOR



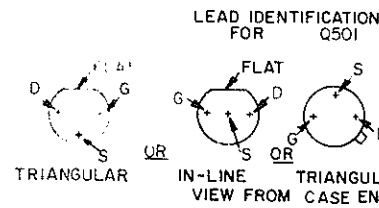
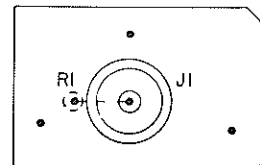
(19C327759, Rev. 1)  
(19B219444, Sh. 1, Rev. 2)  
(19B219444, Sh. 2, Rev. 2)

## A301A ANT INPUT (FLOATING GROUND)



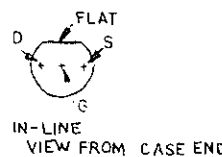
(19B219449, Sh. 1, Rev. 3)  
(19B219449, Sh. 2, Rev. 3)

## A301B ANT INPUT (NON FLOATING GROUND)



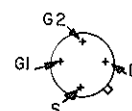
NOTE: LEAD ARRANGEMENT, AND NOT  
CASE SHAPE, IS DETERMINING  
FACTOR FOR LEAD IDENTIFICATION.

### LEAD IDENTIFICATION FOR Q502, Q503

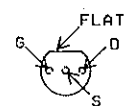


NOTE: LEAD ARRANGEMENT, AND NOT  
CASE SHAPE, IS DETERMINING  
FACTOR FOR LEAD IDENTIFICATION.

### Q520, Q551, Q552

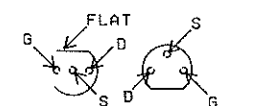


### LEAD IDENTIFICATION FOR Q1



BOTTOM VIEW

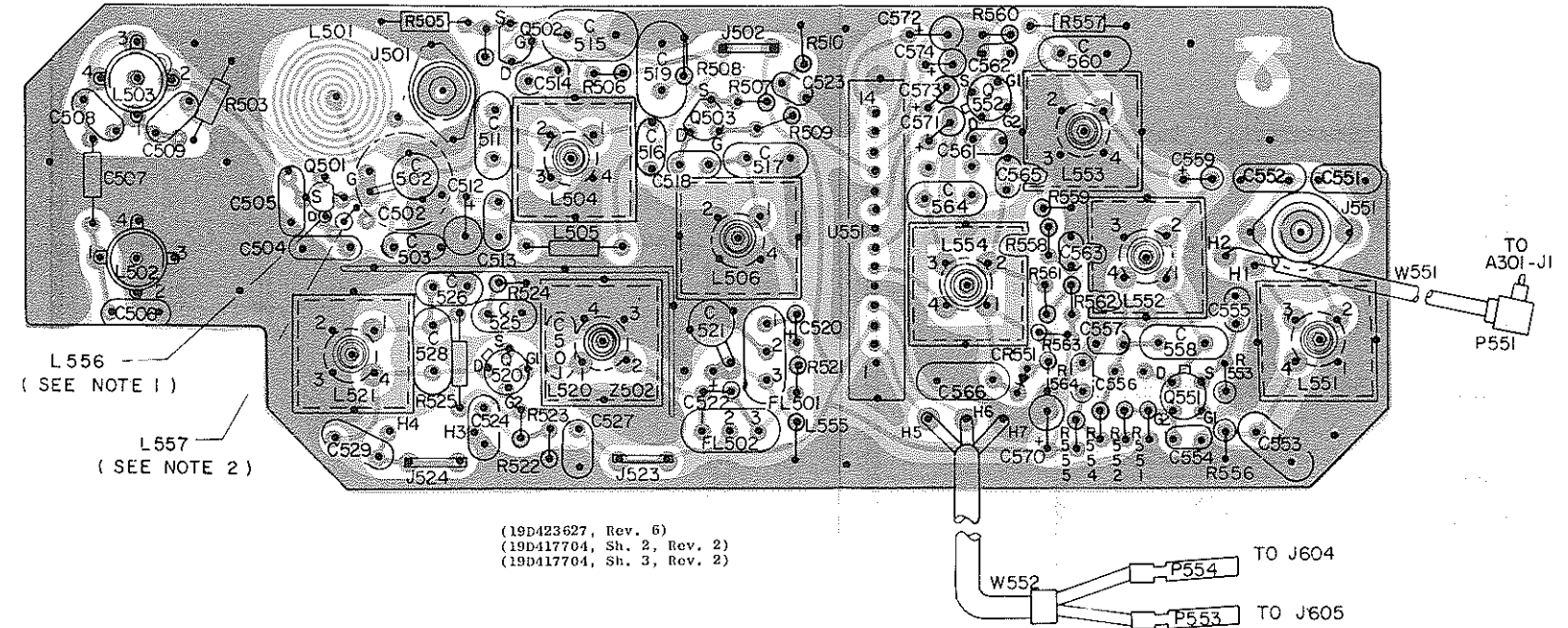
### LEAD IDENTIFICATION FOR Q2, & Q3

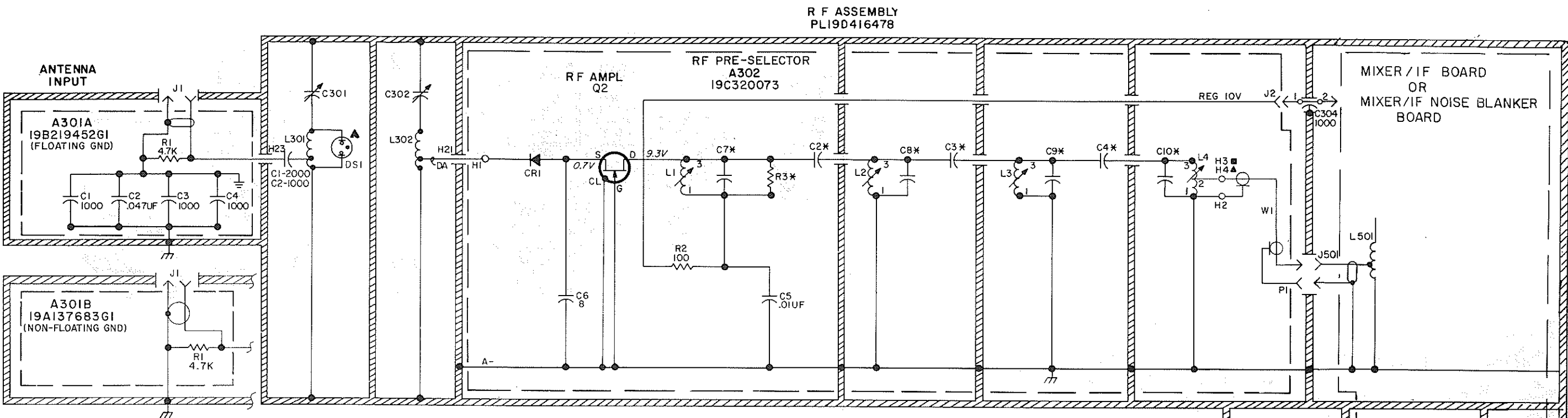


IN-LINE TRIANGULAR  
TOP VIEW

NOTE: LEAD ARRANGEMENT, AND NOT  
CASE SHAPE, IS DETERMINING  
FACTOR FOR LEAD IDENTIFICATION.

## MIXER/IF BLANKER BOARD 19D416562





* COMPONENT VALUE TABLE				
COMP DESIG	LL	L	M	H
RF FREQ	25-30 MHZ	30-36 MHZ	36-42 MHZ	42-50 MHZ
IF FREQ	11.2 MHZ	9.4 MHZ	11.2 MHZ	9.4 MHZ
C2	1.0	.75	.68	.82
C3	1.0	.75	.68	.82
C4	1.0	.75	.68	.82
C7	51	39	30	18
C8	51	39	30	18
C9	51	39	30	18
C10	56	39	30	18
R3			24K	6.2K

MID BAND		
* COMPONENT VALUE TABLE		
SPLIT	ML LOW	MH HIGH
RF FREQ	66-78 MHZ	77-88 MHZ
IF FREQ	11.2 MHZ	11.2 MHZ
C2	.47	.39
C3	.56	.47
C4	1.0	.82
C7	15	10
C8	18	13
C9	18	13
C10	18	13
R3	6.8K	6.8K

RF ASSEMBLY		RF PRE-SELECTOR		ANTENNA INPUT		FREQ (MHZ)
	REV LTR		REV LTR		REV LTR	
19D416478G1	C	19C320073G1	C	19B219452G1	-	25-30 (LL)
19D416478G2	C	19C320073G2	F	19B219452G1	-	30-36 (L)
19D416478G3	B	19C320073G3	E	19B219452G1	-	36-42 (M)
19D416478G4	B	19C320073G4	C	19B219452G1	-	42-50 (H)
19D416478G8	-	19C320073G8	-	19B219452G1	-	66-78 (ML)
19D416478G9	-	19C320073G9	-	19B219452G1	-	77-88 (MH)
19D416478G10	-	19C320073G1	C	19B219452G1	-	25-30 (LL)
19D416478G11	-	19C320073G2	F	19A137683G1	-	30-36 (L)
19D416478G12	-	19C320073G3	E	19A137683G1	-	36-42 (M)
19D416478G13	-	19C320073G4	C	19A137683G1	-	42-50 (H)
19D416478G14	-	19C320073G8	-	19A137683G1	-	66-78 (ML)
19D416478G15	-	19C320073G9	-	19A137683G1	-	77-88 (MH)

VOLTAGE READINGS

VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3A11 OR A 20,000 OHM-PER-VOLT METER.

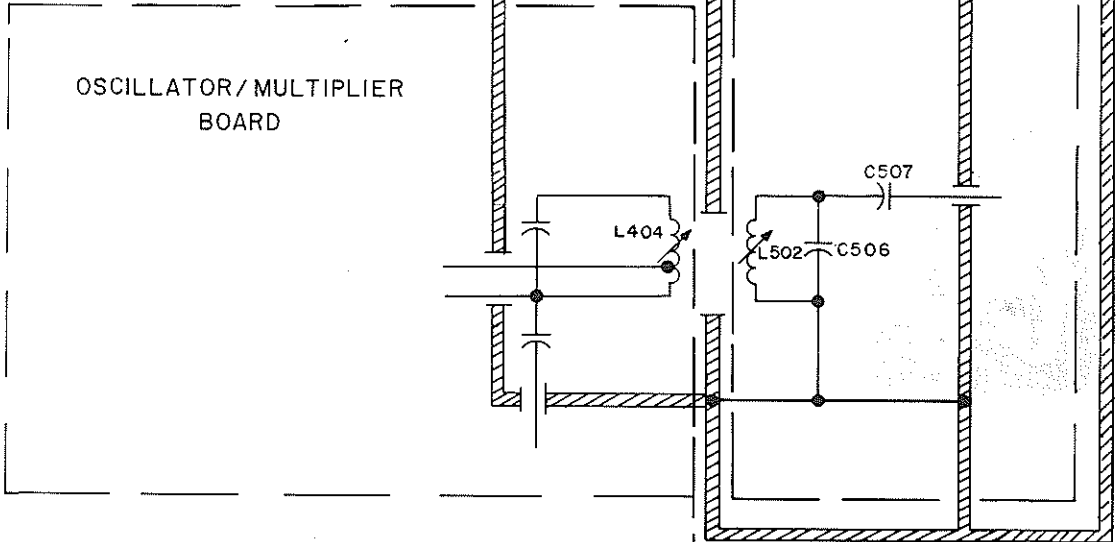
⏏ INDICATES A-

⏏ INDICATES VEHICLE GROUND

ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

CPD 310A

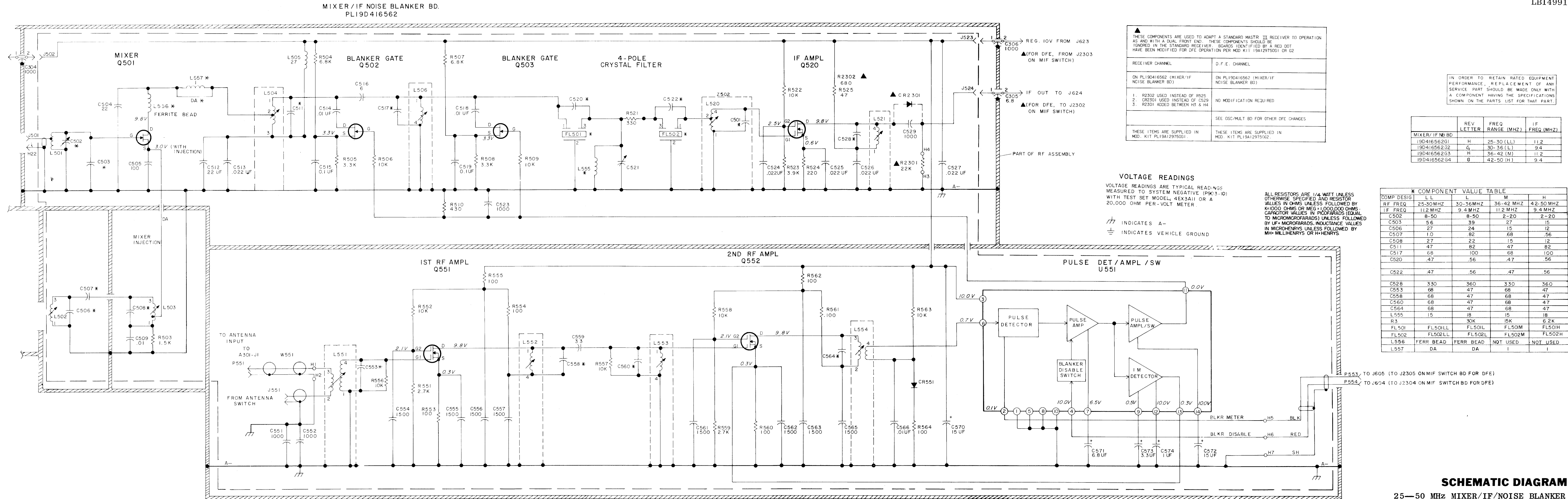
IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.



▲ NOT PRESENT IN M.B.  
■ NOT PRESENT IN L.B.

SCHEMATIC DIAGRAM

25-50 MHz RF AMPLIFIER ASSEMBLY





PARTS LIST		
LBI4992E		
25-30 MHz		
RF ASSEMBLY 19D41047801-G4, G10-G13		
AND		
MIXER/IF/NOISE BLANKER		
19D41656201-G4		

SYMBOL	GE PART NO.	DESCRIPTION
A301A	COMPONENT BOARD 19D21945201	
	----- CAPACITORS -----	
	C1	19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
	C2	19A116080P5 Polyester: 0.047 pf ±20%, 50 VDCW.
	C3 and C4	19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
	----- JACKS AND RECEPTACLES -----	
	J1	19A1130924G1 Connector, receptacle: sim to Cinch 14H11813.
	----- RESISTORS -----	
	R1	3R152P47J2 Composition: 4.7K ohms ±5%, 1/4 w.
	----- JACKS AND RECEPTACLES -----	
A301B	ANTENNA PLATE ASSEMBLY 19A13758G01	
	----- JACKS AND RECEPTACLES -----	
	J1	7104941P20 Connector, jack: sim to National Tel.
	----- RESISTORS -----	
	R1	3R152P47J2 Composition: 4.7K ohms ±5%, 1/4 w.
A302	COMPONENT BOARD A302LL 19C32007361 25-30 MHz (LL) A302L 19C32007362 30-36 MHz (L) A302M 19C32007363 36-42 MHz (M) A302H 19C32007364 42-50 MHz (H)	
	----- CAPACITORS -----	
	C2LL*	5491601P120 Phenolic: 1.0 pf ±5%, 500 VDCW.
	C2L*	5491601P122 Phenolic: 1.2 pf ±5%, 500 VDCW.
	C2L*	5491601P118 Phenolic: 0.75 pf ±5%, 500 VDCW.
	C10W	5491601P120 In REV A & earlier: Phenolic: 1.0 pf ±5%, 500 VDCW.
	C2H*	5491601P117 Phenolic: 0.68 pf ±5%, 500 VDCW.
	C2H*	5491601P119 Phenolic: 0.82 pf ±5%, 500 VDCW.
	C3LL*	5491601P120 Phenolic: 1.0 pf ±5%, 500 VDCW.
	C3L*	5491601P118 Phenolic: 0.75 pf ±5%, 500 VDCW.
A301	COMPONENT BOARD 19D21945201	
	----- CAPACITORS -----	
	C1	19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
	C2	19A116080P5 Polyester: 0.047 pf ±20%, 50 VDCW.
	C3 and C4	19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
	----- JACKS AND RECEPTACLES -----	
	J1	19A1130924G1 Connector, receptacle: sim to Cinch 14H11813.
	----- RESISTORS -----	
	R1	3R152P47J2 Composition: 4.7K ohms ±5%, 1/4 w.
	----- JACKS AND RECEPTACLES -----	
A301B	ANTENNA PLATE ASSEMBLY 19A13758G01	
	----- JACKS AND RECEPTACLES -----	
	J1	7104941P20 Connector, jack: sim to National Tel.
	----- RESISTORS -----	
	R1	3R152P47J2 Composition: 4.7K ohms ±5%, 1/4 w.
A302	COMPONENT BOARD A302LL 19C32007361 25-30 MHz (LL) A302L 19C32007362 30-36 MHz (L) A302M 19C32007363 36-42 MHz (M) A302H 19C32007364 42-50 MHz (H)	
	----- CAPACITORS -----	
	C2LL*	5491601P120 Phenolic: 1.0 pf ±5%, 500 VDCW.
	C2L*	5491601P122 Phenolic: 1.2 pf ±5%, 500 VDCW.
	C2L*	5491601P118 Phenolic: 0.75 pf ±5%, 500 VDCW.
	C10W	5491601P120 In REV A & earlier: Phenolic: 1.0 pf ±5%, 500 VDCW.
	C2H*	5491601P117 Phenolic: 0.68 pf ±5%, 500 VDCW.
	C2H*	5491601P119 Phenolic: 0.82 pf ±5%, 500 VDCW.
	C3LL*	5491601P120 Phenolic: 1.0 pf ±5%, 500 VDCW.
	C3L*	5491601P118 Phenolic: 0.75 pf ±5%, 500 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
C3M*	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW. In REV C and earlier:
C3H*	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
C4LL*	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
C4L*	5491601P122	Phenolic: 1.2 pf ±5%, 500 VDCW.
	5491601P118	Phenolic: 0.75 pf ±5%, 500 VDCW.
C4H*	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.
C4M*	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
C5	19A116090P101	Polyester: 0.01 pf ±10%, 50 VDCW.
	19A116655P8KH	Ceramic: 8 pf ±1 pf ±10%, ±80 PPM.
C7LL	5496219P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM.
C7L	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.
C7M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C7H	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C8LL	5496219P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM.
C8L	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.
C8M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C8H	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C9LL	5496219P256	Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef -80 PPM.
C9L	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.
C9M	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C9H	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C10LL	5496219P253	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef -80 PPM.
C10L	5496219P250	Ceramic disc: 30 pf ±5%, 500 VDCW, temp coef -80 PPM.
C10H	5496219P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.
C1H	19A116052P2	Silicon, Hot Carrier: Fwd. drop .410 volts max.
	19A116975P1	Receptacle, wire spring.
L1*	19C30710P306	Coil, RF: variable; sim to Paul Smith 092574-D8-3.
	19B219419G2	Coil, Includes:
C501L	5491798P5	Tuning slug.
	5491798P5	Tuning slug.

SYMBOL	GE PART NO.	DESCRIPTION
L4*	19C30710P306	Coil, RF: variable; sim to Paul Smith 071774-C0-7.
C502M	19B219419G1	Coil, Includes:
	5491798P5	Tuning slug.
P1	19A116960P1	N Type, field effect: sim to 2M4416.
	19A116960P1	N Type, field effect: sim to 2M4416.
R2	3R152P101J	Composition: 100 ohms ±5%, 1/4 w.
	3R152P303J	Composition: 30K ohms ±5%, 1/4 w. Deleted by REV B.
R3M*	19A116655P22J3	Composition: 24K ohms ±5%, 1/4 w. Deleted by REV C.
	3R152P153J	Composition: 15K ohms ±5%, 1/4 w. Deleted by REV B.
R3H	3R152P422J	Composition: 6.2K ohms ±5%, 1/4 w.
	5491689P85	Cable, RF: approx 4 inches long. (Includes P1).
C301	19A116192P10	Ceramic: 22 pf ±5%, temp coef -80 PPM.
	19A116655P22J3	Composition: 24K ohms ±5%, 1/4 w. Deleted by REV C.
C302	19A116655P15J3	Ceramic: 15 pf ±5%, temp coef -80 PPM.
	19A116655P12J3	Ceramic: 12 pf ±5%, temp coef -80 PPM.
C304	19A116655P15J4	Ceramic: 12 pf ±5%, temp coef -80 PPM.
	19A116655P12J4	Ceramic: 12 pf ±5%, temp coef -80 PPM.
C305	19A116655P12J1	Polyester: 0.01 pf ±10%, 50 VDCW.
	19A116655P12J1	Polyester: 0.01 pf ±10%, 50 VDCW.
C306	19B209488P2	Ceramic, feed-thru: 1000 pf ±100 -0-, 500 VDCW; sim to Allen-Bradley Style FASD.
	19B209488P1	Ceramic, feed-thru: 6.8 pf ±20%, 500 VDCW; sim to Allen-Bradley Style FASD.
C308	19B209488P2	Ceramic, feed-thru: 1000 pf ±100 -0-, 500 VDCW; sim to Allen-Bradley Style FASD.
	19B209488P1	Ceramic, feed-thru: 6.8 pf ±20%, 500 VDCW; sim to Allen-Bradley Style FASD.
C311L	5490008P125	Silver mica: 82 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
	5490008P119	Silver mica: 47 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C311H	5490008P125	Silver mica: 82 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
	5490008P119	Silver mica: 47 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C312	5494818P13	Capacitor, ceramic disc: 2000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
	5494818P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
D8L	19B209067P1	Lamp, glow: 0.7 ma; sim to GE NEZET.
	19B219455G2	Coil, Includes:
C2	5494818P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
	19B219455G2	Coil, Includes:
C10H	19B219455G4	Coil, Includes:
	19B219455G4	Coil, Includes:
J2	19A116975P1	Receptacle, wire spring.
	19A116975P1	Receptacle, wire spring.
L1*	19C30710P306	Coil, RF: variable; sim to Paul Smith 092574-D8-3.
	19B219419G2	Coil, Includes:
C501L	5491798P5	Tuning slug.
	5491798P5	Tuning slug.

SYMBOL	GE PART NO.	DESCRIPTION
C502LL and C502L	5490046P1	Variable, ceramic: approx 8-50 pf, 350 VDCW, temp coef -750 PPM; sim to Erie Style 357-36.
C502M and C502H	19B209351P2	Variable, ceramic: 2.5 to 20 pf, 200 VDCW, temp coef -250 +700 PPM/°C; sim to Matsushita KCV-14K02P2.
C503LL	5490008P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C503L	5490008P17	Silver mica: 39 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C503M	5490008P13	Silver mica: 27 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C503H	5490008P8	Silver mica: 15 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C504	19A116655P22J3	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef 0 PPM.
C505	5490008P27	Silver mica: 100 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C506LL	19A116655P27J3	Ceramic: 27 pf ±5%, temp coef -80 PPM.
C506L	19A116655P22J3	Ceramic: 22 pf ±5%, temp coef -80 PPM.
C506M	19A116655P15J3	Ceramic: 15 pf ±5%, temp coef -80 PPM.
C506H	19A116655P12J3	Ceramic: 12 pf ±5%, temp coef -80 PPM.
C507LL	5491601P120	Phenolic: 1.0 pf ±5%, 500 VDCW.
C507L	5491601P119	Phenolic: 0.82 pf ±5%, 500 VDCW.
C507M	5491601P117	Phenolic: 0.68 pf ±5%, 500 VDCW.
C507H	5491601P115	Phenolic: 0.56 pf ±5%, 500 VDCW.
C508LL	19A116655P27J3	Ceramic: 27 pf ±5%, temp coef -80 PPM.
C508L	19A116655P22J4	Ceramic: 22 pf ±5%, temp coef -80 PPM.
C508M	19A116655P15J4	Ceramic: 15 pf ±5%, temp coef -80 PPM.
C508H	19A116655P12J4	Ceramic: 12 pf ±5%, temp coef -80 PPM.
C509	19A116655P12J1	Polyester: 0.01 pf ±10%, 50 VDCW.
C511LL	5490008P119	Silver mica: 47 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C511M	5490008P119	Silver mica: 47 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C511H	5490008P125	Silver mica: 82 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C512	5496267P10	Tantalum: 22 pf ±20%, 15 VDCW; sim to Sprague Type 150D.
C513	19A116080P3	Polyester: 0.022 pf ±20%, 50 VDCW.
C514	19A116080P101	Polyester: 0.01 pf ±10%, 50 VDCW.
C515	19A116080P107	Polyester: 0.01 pf ±10%, 50 VDCW.
C516	19A116655P6J0	Ceramic disc: 6 pf ±20.5 pf, 500 VDCW, temp coef 0 PPM.
C517L*	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C517H	5490008P119	In REV G & earlier:
	5490008P127	Silver mica: 47 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C517L	5490008P127	Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C517M*	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C565	19A116192P10	Ceramic: 1500 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W8R-152K.
	19A116080P107	Polyester: 0.1 pf ±10%, 50 VDCW.
C566	5490008P127	Silver mica: 100 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C571	5496267P14	Tantalum: 15 pf ±20%, 20 VDCW; sim to Sprague Type 150D.
C571	5496267P1	Tantalum: 6.8 pf ±20%, 6 VDCW; sim to Sprague Type 150D.
C5719	19A116080P101	Polyester: 0.01 pf ±10%, 50 VDCW.
C520LL	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.
C520L	5491601P113	Phenolic: 0.56 pf ±5%, 500 VDCW.
C520M	5491601P113	Phenolic: 1.0 pf ±5%, 500 VDCW.
C520H	5491601P115	Phenolic: 0.56 pf ±5%, 500 VDCW.
C521	19B209351P2	Variable: 2.5 to 20 pf, 200 VDCW, -250 +700 PPM/°C; sim to Matsushita KCV-14K02P2.
C522LL	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.
C522L	5491601P113	Phenolic: 0.56 pf ±5%, 500 VDCW.

SYMBOL	GE PART NO.	DESCRIPTION
C522M	5491601P113	Phenolic: 0.47 pf ±5%, 500 VDCW.
C522H	5491601P115	Phenolic: 0.56 pf ±5%, 500 VDCW.
C523	19A116192P13	Ceramic: 1000 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W8R-102K.
C524 thru C527	19A116080P3	Polyester: 0.022 pf ±20%, 50 VDCW.
C528LL	5490008P39	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C528L	5490008P40	Silver mica: 360 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C528M	5490008P39	Silver mica: 330 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C528H	5490008P40	Silver mica: 360 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C529	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C531 and C532	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C533LL	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C533L	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C533M	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C533H	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C534 thru C537	19A116192P10	Ceramic: 1500 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W8R-152K.
C538LL	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C538L	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C538M	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C538H	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C539	5491601P130	Phenolic: 3.3 pf ±5%, 500 VDCW.
C560LL	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C560L	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C560M	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C560H	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C561 thru C563	19A116192P10	Ceramic: 1500 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W8R-152K.
C564LL	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C564L	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C564M	5490008P23	Silver mica: 68 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C564H	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
C565	19A116192P10	Ceramic: 1500 pf ±10%, 50 VDCW; sim to Erie 8121-A050-W8R-152K.
C566	19A116080P107	Polyester: 0.01 pf ±10%, 50 VDCW.
C570	5496267P14	Tantalum: 15 pf ±20%, 20 VDCW; sim to Sprague Type 1500.
C571	5496267P1	Tantalum: 6.8 pf ±20%, 6 VDCW; sim to Sprague Type 1500.
C572	5496267P14	Tantalum: 15 pf ±20%, 20 VDCW; sim to Sprague Type 1500.
C573	5496267P19	Tantalum: 3.3 pf ±20%, 15 VDCW; sim to Sprague Type 1500.
C574	5496267P17	Tantalum: 1.0 pf ±20%, 35 VDCW; sim to Sprague Type 1500.
C551	19A115775P1	- - - - - DIODES AND RECTIFIERS - - - - - Silicon, fast recovery, 225 mA, 50 PIV.

SYMBOL	GE PART NO.	DESCRIPTION
Z502H		COIL ASSEMBLY 19C320141G27
		- - - - - CAPACITORS - - - - -
C501H	19A700220P64	Ceramic: 100 pf $\pm 10\%$ , 100 VDCW; temp coef -3300 PPM.
		- - - - - INDUCTORS - - - - -
L520H	19C320141P26	Coil. Includes:
	19B209674P2	Tuning slug.
		- - - - - MISCELLANEOUS - - - - -
	19B219470P2	Shield.
	19A129424G1	Can. (Used with L504, L506, L520, L521, L551-L554).
	4031594P1	Insulator. (Used with C521).
	4035306P23	Insulator, fiber. (Used with J501).
	4035306P59	Insulator, fiber. (Used with L501).
		DUAL FRONT END MOD KIT 19A129750G1 RECEIVER 19A129750G2 DFE
		- - - - - CAPACITORS - - - - -
C2301*	19A116556P8J0	Ceramic disc: 8 pf $\pm 0.5$ pf, 500 VDCW, temp coef 0 PPM. Deleted by REV B.
		- - - - - DIODES AND RECTIFIERS - - - - -
CR2301	19A116925P1	Silicon, pin: 35 volt Reverse Breakdown, 400 mw.
		- - - - - RESISTORS - - - - -
R2301	19A700106P95	Composition: 22K ohms $\pm 5\%$ , 1/4 w.
R2302	19A700106P59	Composition: 680 ohms $\pm 5\%$ , 1/4 w.
R2303	3R152P911J	Composition: 910 ohms $\pm 5\%$ , 1/4 w.
		- - - - - CABLES - - - - -
R2301	19B219999G2	Cable: approx 10-1/2 inches long.



## PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A thru E - Mixer/IF/Noise Blanker Board 19D416562G1, 2
- REV. A thru D - Mixer/IF/Noise Blanker Board 19D416562G3, 4
- REV. A - RF Filter Board 19C320073G1-4  
The above revisions incorporated in initial shipment.
- REV. B - RF Filter Board 19C320073G2 & 3  
To improve receiver sensitivity. Deleted R3L and R3M.
- REV. C - RF Filter Board 19C320073G3  
To prevent oscillation. Added R3M.
- REV. B - RF Filter Board 19C320073G1, 4
- REV. C - RF Filter Board 19C320073G2
- REV. D - RF Filter Board 19C320073G3  
To improve receiver sensitivity. Changed C2, C3 and C4 and L1 thru L4.
- REV. F - Mixer/IF/Noise Blanker Board 19D416562G1, 2
- REV. E - Mixer/IF/Noise Blanker Board 19D416562G3, 4  
To improve blanker operation. Changed Q502 and Q503.
- REV. G - Mixer/IF/Noise Blanker Board 19D416562G1, 2
- REV. F - Mixer/IF/Noise Blanker Board 19D416562G3, 4  
To improve operation. Added L556.
- REV. A & B - RF Assembly 19D416478G1-4  
Incorporated in initial shipment.
- REV. C - RF Assembly 19D416478G1, 2  
To improve sensitivity in 25-30 MHz range. Changed C1 (part of L301).
- REV. D - RF Filter Board 19C320073G2  
To prevent oscillations in pre-selector board  
Added R3L.
- REV. G - Mixer/IF/Noise Blanker 19D416562G3, 4  
To prevent oscillations in mixer. Replace L556 with L557. Connected C504 to Q501D.
- REV. C - RF Filter Board 19C320073G1, G4
- REV. E - RF Filter Board 19C320073G2, G3  
To standardize components. Deleted Q1 and PWB 19C320072. Added Q2 and PWB 19C327760P1.
- REV. H - Mixer/IF/Noise Blanker 19D416562G1 & G3  
To improve operation in the 25-30 MHz and 36-42 MHz range. Changed C517.